

# MRF16006



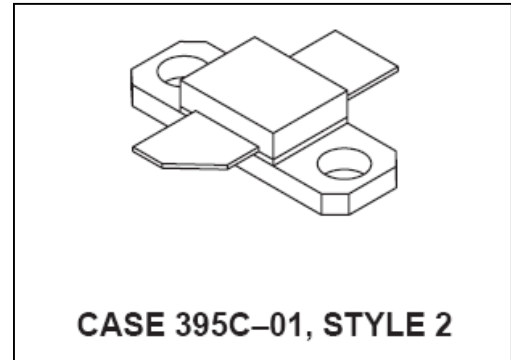
The RF Line NPN Silicon Power Transistor  
6.0W , 1.6GHz, 28V

M/A-COM Products  
Released - Rev. 07.07

## Product Image

Designed for 28 V microwave large-signal, common base, Class C, CW amplifier applications in the range 1600 – 1640 MHz.

- Specified 28 V, 1.6 GHz Class C characteristics
  - Output power = 6 W
  - Minimum gain = 7.4 dB, @ 6 W
  - Minimum efficiency = 40% @ 6 W
- Characterized with series equivalent large-signal parameters from 1500 MHz to 1700 MHz
- Silicon nitride passivated
- Gold metalized, emitter ballasted for long life and resistance to metal migration



## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

| Rating  | Symbol           | Value       | Unit          |
|---|------------------|-------------|---------------|
| Collector-Emitter Voltage   | V <sub>CES</sub> | 60          | Vdc           |
| Emitter-Base Voltage  | V <sub>EBO</sub> | 4.0         | Vdc           |
| Collector-Current   | I <sub>C</sub>   | 1.0         | Adc           |
| Total Device Dissipation @ T <sub>C</sub> = 25°C<br>Derate above 25°C | P <sub>D</sub>   | 26<br>0.15  | Watts<br>W/°C |
| Storage Temperature Range   | T <sub>stg</sub> | -65 to +150 | °C            |

## THERMAL CHARACTERISTICS

|   |                  |     |      |
|---|------------------|-----|------|
| Thermal Resistance — Junction to Case (1) (2) | R <sub>θJC</sub> | 6.8 | °C/W |
|---|------------------|-----|------|

(1) Thermal measurement performed using CW RF operating condition.

(2) Thermal resistance is determined under specified RF operating conditions by infrared measurement techniques.

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**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

**OFF CHARACTERISTICS**

|   |               |     |   |     |      |
|---|---------------|-----|---|-----|------|
| Collector–Emitter Breakdown Voltage<br>( $I_C = 40 \text{ mAdc}$ , $V_{BE} = 0$ ) | $V_{(BR)CES}$ | 55  | — | —   | Vdc  |
| Collector–Base Breakdown Voltage<br>( $I_C = 40 \text{ mAdc}$ , $I_E = 0$ )       | $V_{(BR)CBO}$ | 55  | — | —   | Vdc  |
| Emitter–Base Breakdown Voltage<br>( $I_E = 2.5 \text{ mAdc}$ , $I_C = 0$ )        | $V_{(BR)EBO}$ | 4.0 | — | —   | Vdc  |
| Collector Cutoff Current<br>( $V_{CE} = 28 \text{ Vdc}$ , $V_{BE} = 0$ )          | $I_{CES}$     | —   | — | 2.5 | mAdc |

**ON CHARACTERISTICS**

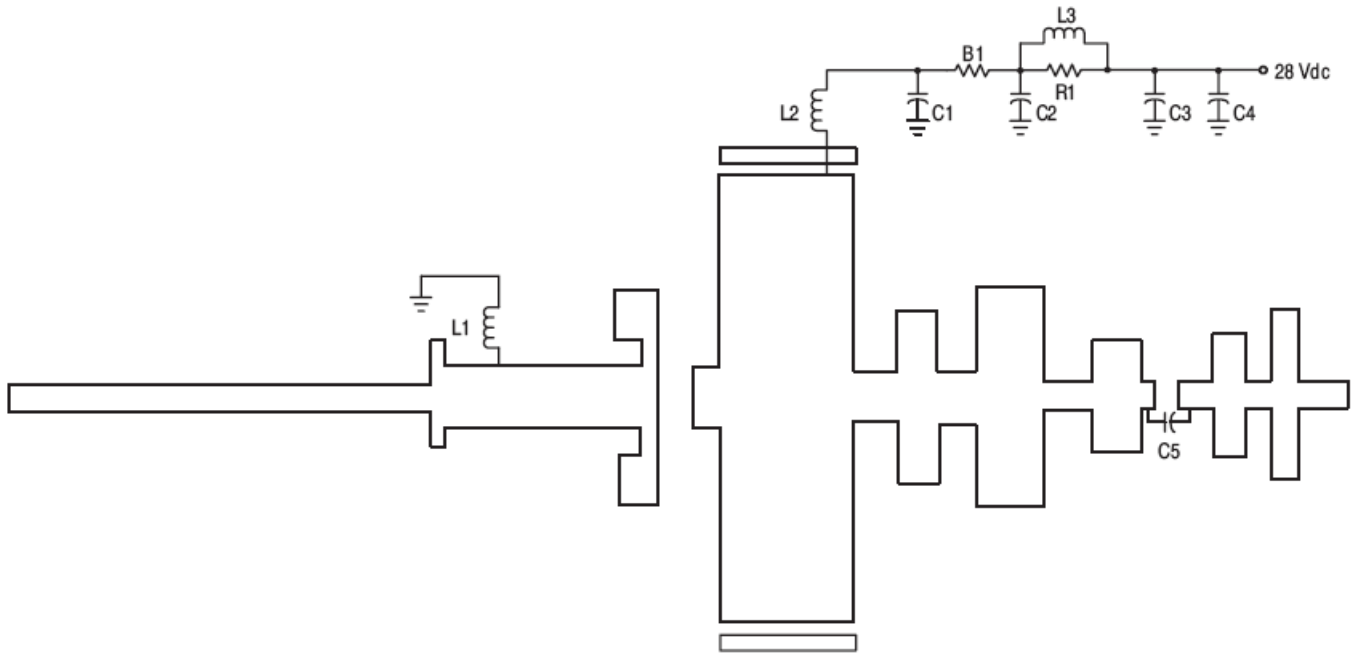
|  |          |    |   |    |   |
|--|----------|----|---|----|---|
| DC Current Gain<br>( $I_{CE} = 0.2 \text{ Adc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) | $h_{FE}$ | 20 | — | 80 | — |
|--|----------|----|---|----|---|

**DYNAMIC CHARACTERISTICS**

|   |          |    |   |   |    |
|---|----------|----|---|---|----|
| Output Capacitance<br>( $V_{CB} = 28 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ ) | $C_{ob}$ | 11 | — | — | pf |
|---|----------|----|---|---|----|

**FUNCTIONAL TESTS**

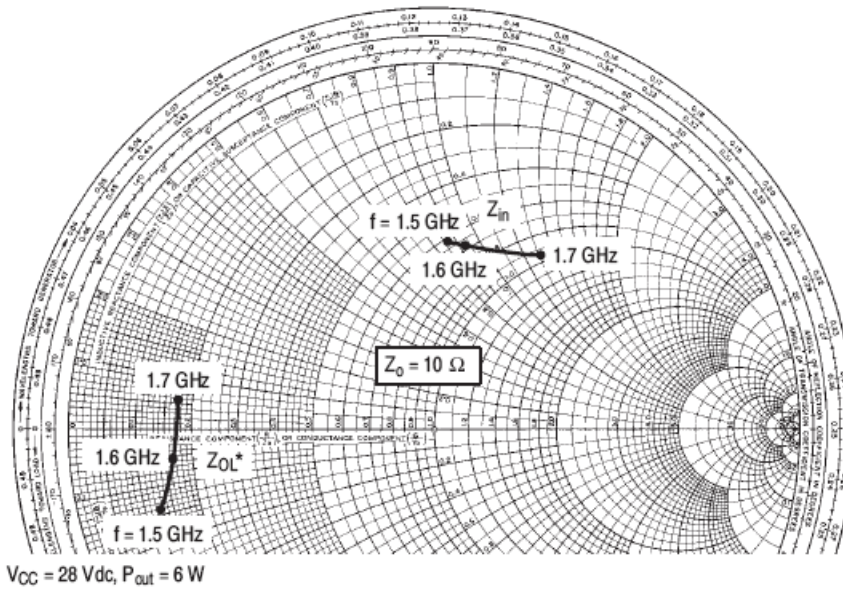
|   |          |                                |     |   |    |
|---|----------|--------------------------------|-----|---|----|
| Common–Base Amplifier Power Gain<br>( $V_{CC} = 28 \text{ Vdc}$ , $P_{out} = 6 \text{ Watts}$ , $f = 1600/1640 \text{ MHz}$ )   | $G_{pe}$ | 7.4                            | —   | — | dB |
| Collector Efficiency<br>( $V_{CC} = 28 \text{ Vdc}$ , $P_{out} = 6 \text{ Watts}$ , $f = 1600/1640 \text{ MHz}$ )   | $\eta$   | 40                             | 45  | — | %  |
| Return Loss<br>( $V_{CC} = 28 \text{ Vdc}$ , $P_{out} = 6 \text{ Watts}$ , $f = 1600/1640 \text{ MHz}$ )  | $I_{RL}$ | —                              | 8.0 | — | dB |
| Output Mismatch Stress<br>( $V_{CC} = 28 \text{ Vdc}$ , $P_{out} = 6 \text{ Watts}$ , $f = 1600 \text{ MHz}$ , Load VSWR = 3:1 all phase angles at frequency of test) | $\psi$   | No Degradation in Output Power |     |   |    |



Board Material – Teflon<sup>®</sup> Glass Laminate Dielectric  
Thickness – 0.30",  $\epsilon_r = 2.55$ ", 2.0 oz. Copper

|        |                              |        |                                      |
|--------|------------------------------|--------|--------------------------------------|
| B1     | Fair Rite Bead on #24 Wire   | C4     | 47 $\mu$ F, 50 V, Electrolytic Cap   |
| C1, C5 | 100 pF, B Case, ATC Chip Cap | L1, L2 | 3 Turns, #18, 0.133" ID, 0.15" Long  |
| C2     | 0.1 $\mu$ F, Dipped Mica Cap | L3     | 9 Turns, #24 Enamel                  |
| C3     | 0.1 $\mu$ F, Chip Cap        | R1     | 82 $\Omega$ , 1.0 W, Carbon Resistor |

Figure 1. MRF16006 Test Fixture Schematic



| f<br>MHz | $Z_{in}$<br>Ohms | $Z_{OL}^*$<br>Ohms |
|----------|------------------|--------------------|
| 1500     | $6.28 + j 8.53$  | $1.22 - j 1.37$    |
| 1600     | $7.04 + j 9.00$  | $1.58 - j 0.53$    |
| 1700     | $9.55 + j 12.86$ | $1.71 + j 0.39$    |

$Z_{OL}^*$  = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 2. Series Equivalent Input/Output Impedance

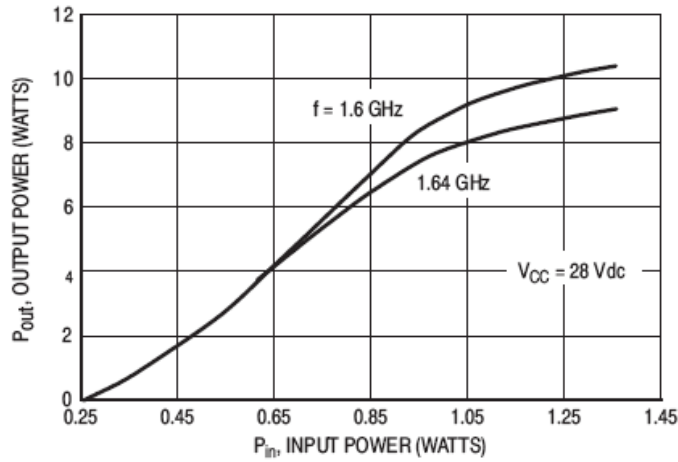


Figure 3. Output Power versus Input Power

## PACKAGE DIMENSIONS

